

V1.1 Datasheet

PRODUCTY SUMMARY

48

45

63

RDS(on) $m(\Omega)$ Max

 $@V_{GS}=10V$

@V_{GS}=4.5V

 $@V_{GS}=-10V$

@V_{GS}=-4.5V

N+P-Channel 40V MOSFET

FEATURES

- Advance Trench Process Technology
- ●High Density Cell Design for Ultra Low On-resistance

Application

- ■Portable Devices
- ■Consumer Electronics

Mechanical

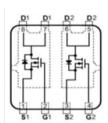
●Case:DFN5060 Package

DFN5060

 V_{DS}

40

-40



Packing Information

Package	Packing
DFN5060	3K/13" Reel

Maximum Ratings (T _A =25°C unless otherwise specified)							
Parameter	Symbol	Lin	Limit				
	Symbol	N-Channel	P-Channel	Unit			
Gate-Source Voltage	V_{DS}	40	-40	V			
Gate-Source Voltage	V_{GS}	±20	±20	Α			
Continuous Drain Current 1)	I _{DSM}	14	-11	А			
Continuous Drain Current 4)	I _D	56	-44	Α			
Continuous Drain Current 5)	I _{DM}	79	-66	Α			
Maximum Power Dissipation	P_D	6	6	W			
Operating Junction and Storage Temperature Range	T_J, T_STG	-55 to 150	-55 to 150	°C			

Typical Thermal Resistance							
Parameter Symbol Limit Unit							
Junction-to-Ambient Thermal Resistance 3)	$R_{\theta JA}$	34	°C/W				

Note:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Fused current that based on wire numbers and diameter.
- 3. Guaranteed by design, not subject to production testing.
- 4. The maximum current rating is package limited.
- 5. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keepinitial T_J =25°C.

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Electrical Characteristics (TA = 25°C UNLESS OTHERWISE NOTED)						
Characteristics	Symbol	Test Condition	Limits			Unit
			Min	Тур	Max	Offic
	N-	Channel Static				
Drain-Source Breakdown Voltage	B _{VDSS}	V_{GS} =0V, I_D =250uA	40			V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250uA$	1.0	1.6	2.0	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10.0V, I _D =13A	-	25	31	mΩ
		V _{GS} =4.5V, I _D =11A	-	39	48	mΩ
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	1.0	uA
Gate-Source Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
Drain-Source Diode						
Maximum Continuous Body Diode Forward Current	I _S	-	-	-	1.2	А
Diode Forward Voltage	V_{SD}	I _S =1.0A, V _{GS} =0V	-	-	1.5	V

Electrical Characteristics (T _A = 25°C UNLESS OTHERWISE NOTED)						
Characteristics	Symbol	Test Condition	Limits			l lmit
			Min	Тур	Max	Unit
	P-	Channel Static				
Drain-Source Breakdown Voltage	B _{VDSS}	V_{GS} =0V, I_D =-250uA	-40	1	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=-250uA$	-1.0	-	-3.0	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10.0V, I _D =-11A	-	37	45	mΩ
		V _{GS} =-4.5V, ID=-9A	-	51	63	mΩ
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-40V, V _{GS} =0V	-		1.0	uA
Gate-Source Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
Drain-Source Diode						
Maximum Continuous Body Diode Forward Current	I _S	-	-	-	-1.2	А
Diode Forward Voltage	V _{SD}	I _S =-1.0A, V _{GS} =0V	-	-	-1.5	V

Note:

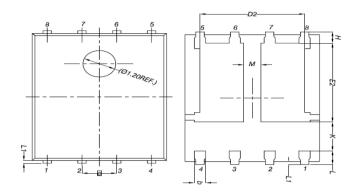
- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. R_{QJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch2 with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.

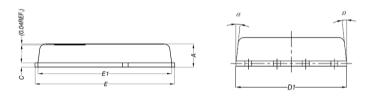
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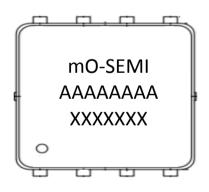
Package Outline Dimensions (inches and millimeters)

DFN5060							
	Dimensions						
SYMBOL	Millir	neters	Inch	ies			
	Min	Max	Min	Max			
Α	0.90	1.10	0.035	0.043			
b	0.33	0.51	0.013	0.020			
С	0.20	0.30	0.008	0.012			
D1	4.80	5.00	0.189	0.197			
D2	3.61	3.96	0.142	0.156			
Е	5.90	6.10	0.232	0.240			
E1	5.70	5.80	0.224	0.228			
E2	3.38	3.78	0.133	0.149			
е	1.27bsc						
Н	0.41	0.61	0.016	0.024			
K	1.100	-	0.043	-			
L	0.51	0.71	0.020	0.028			
L1	0.06	0.20	0.002	0.008			
M	0.50	-	0.020	-			
α	0 °	12 °	-	-			





Marking Information



First line = Company name

AAAAAAA = Product number

XXXXXXX = Tracking number

Fourth line = Pin1 Point

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